

#### **40V NPN MEDIUM POWER PLANAR TRANSISTOR IN SOT23**

#### **Features**

- BV<sub>CEO</sub> > 40V
- I<sub>C</sub> = 1A Continuous Collector Current
- Low Saturation Voltage V<sub>CE(sat)</sub> < 500mV @ 1A</li>
- Complementary Part Number ZXTP2041F
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

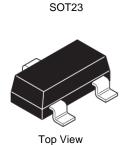
- Case: SOT23
- Case material: Molded Plastic. "Green" Molding Compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Matte Tin Finish; Solderable per MIL-STD-202, Method 208 <sup>®</sup>
- Weight: 0.008 grams (Approximate)

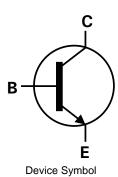
### **Description**

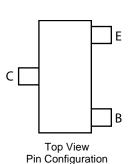
This transistor combines high gain, high current operation and low saturation voltage making it ideal for power MOSFET gate driving and low loss power switching.

### **Applications**

- Power MOSFET date driving
- Low loss power switching







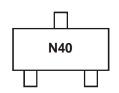
## **Ordering Information** (Note 4)

| I | Part Number | Marking | Reel size (inches) | Tape width (mm) | Quantity per reel |
|---|-------------|---------|--------------------|-----------------|-------------------|
|   | ZXTN2040FTA | N40     | 7                  | 8               | 3,000             |

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
- 2. See http://www.diodes.com for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com.

# **Marking Information**



N40 = Product Type Marking Code



### **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

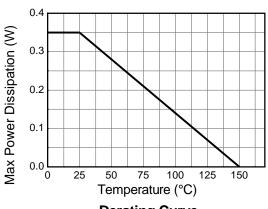
| Characteristic                        | Symbol           | Value | Unit |
|---------------------------------------|------------------|-------|------|
| Collector-Base Voltage                | V <sub>CBO</sub> | 40    | V    |
| Collector-Emitter Voltage             | V <sub>CEO</sub> | 40    | V    |
| Emitter-Base Voltage                  | V <sub>EBO</sub> | 6     | V    |
| Continuous Collector Current (Note 5) | Ic               | 1     | Α    |
| Peak Pulse Current                    | I <sub>CM</sub>  | 2     | Α    |
| Peak Base Current                     | I <sub>BM</sub>  | 1     | Α    |

### **Thermal Characteristics**

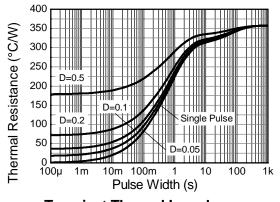
| Characteristic                          | Symbol              | Value           | Unit |        |  |
|---|---------------------|-----------------|------|--------|--|
| Collector Power Dissipation             | (Note 5)            | <u> </u>        | 310  | mW     |  |
| Director Power Dissipation              | (Note 6)            | $P_{D}$         | 350  |        |  |
| Thermal Desigtance Junction to Ambient  | (Note 5)            | <u> </u>        | 403  | 00/11/ |  |
| ermal Resistance, Junction to Ambient   | (Note 6)            | $R_{\theta JA}$ | 357  | °C/W   |  |
| Thermal Resistance, Junction to Leads   | (Note 7)            | $R_{\theta JL}$ | 350  | °C/W   |  |
| Operating and Storage Temperature Range | $T_{J}$ , $T_{STG}$ | -55 to +150     | °C   |        |  |

Notes:

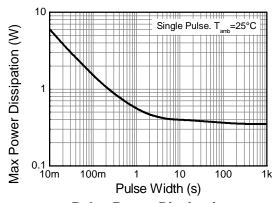
- 5. For the device mounted on minimum recommended pad layout FR4 PCB with high coverage of single sided 1oz copper in still air condition.
- 6. Same as Note 5, expect the device is mounted on 15mm X 15mm X 1.6mm FR4 PCB.
- 7. Thermal resistance from junction to solder-point (at the end of the collector lead).



**Derating Curve** 



**Transient Thermal Impedance** 



**Pulse Power Dissipation** 





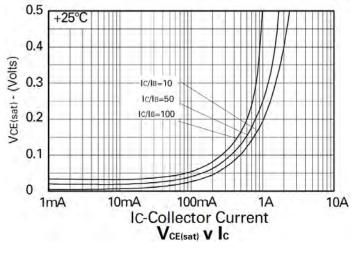
## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

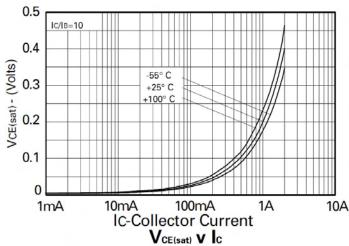
| Characteristic   | Symbol               | Min                     | Тур | Max               | Unit | Test Condition   |
|--|----------------------|-------------------------|-----|-------------------|------|--|
| OFF CHARACTERISTICS                                      |                      |                         |     |                   |      |  |
| Collector-Base Breakdown Voltage                         | $BV_CBO$             | 40                      | _   | _                 | V    | $I_{C} = 100 \mu A$  |
| Collector-Emitter Breakdown Voltage (base open) (Note 8) | BV <sub>CEO</sub>    | 40                      | _   | _                 | V    | I <sub>C</sub> = 10mA  |
| Emitter-Base Breakdown Voltage                           | BV <sub>EBO</sub>    | 6                       | _   | _                 | V    | $I_E = 100\mu A$   |
| Collector-emitter cut-off current                        | I <sub>CES</sub>     | _                       | _   | 100               | nA   | V <sub>CE</sub> = 30V  |
| Collector-base Cut-off Current                           | I <sub>CBO</sub>     | _                       | _   | 100               | nA   | $V_{CB} = 30V$   |
| Emitter-base Cut-off Current                             | I <sub>EBO</sub>     | _                       | _   | 100               | nA   | $V_{EB} = 5V$  |
| ON CHARACTERISTICS (Note 8)                              |                      |                         |     | -                 |      |  |
| Static Forward Current Transfer Ratio                    | h <sub>FE</sub>      | 300<br>300<br>200<br>35 | _   | 900<br>—<br>—     | _    | $\begin{split} I_{C} &= 1 \text{mA}, \ V_{CE} = 5 \text{V} \\ I_{C} &= 500 \text{mA}, \ V_{CE} = 5 \text{V} \\ I_{C} &= 1 \text{A}, \ V_{CE} = 5 \text{V} \\ I_{C} &= 2 \text{A}, \ V_{CE} = 5 \text{V} \end{split}$ |
| Collector-Emitter Saturation Voltage                     | V <sub>CE(sat)</sub> | _                       | _   | 200<br>300<br>500 | mV   | $I_C = 100$ mA, $I_B = 1$ mA<br>$I_C = 500$ mA, $I_B = 50$ mA<br>$I_C = 1$ A, $I_B = 100$ mA   |
| Base-Emitter Saturation Voltage                          | $V_{BE(sat)}$        | _                       | _   | 1.1               | V    | $I_C = 1A$ , $I_B = 100mA$   |
| Base-Emitter On Voltage                                  | V <sub>BE(on)</sub>  | _                       | _   | 1.0               | V    | $I_C = 1A$ , $V_{CE} = 5V$   |
| SMALL SIGNAL CHARACTERISTICS (Note 8)                    |                      |                         |     |                   |      |  |
| Transition Frequency                                     | f⊤                   | 150                     | _   | _                 | MHz  | $I_C = 50$ mA, $V_{CE} = 10$ V,<br>f = 100MHz  |
| Output Capacitance                                       | $C_{obo}$            |                         |     | 10                | pF   | V <sub>CB</sub> = 10V, f = 1MHz  |

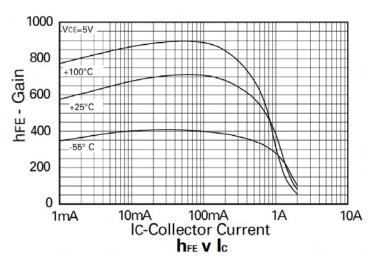
Notes: 8. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$  2%

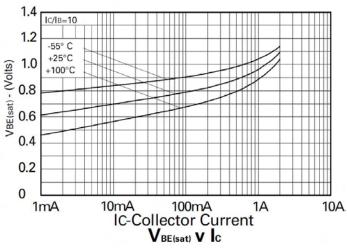


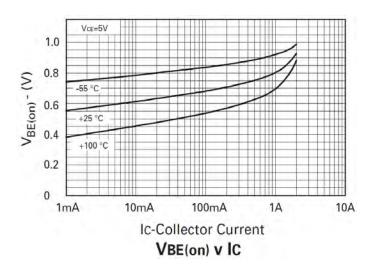
## **Typical Electrical Characteristics**

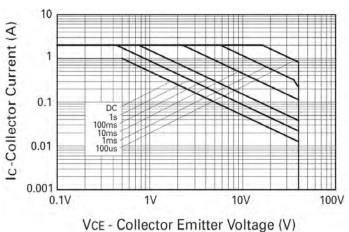








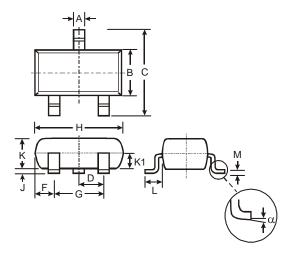






# **Package Outline Dimensions**

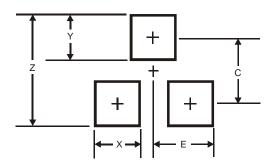
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



| SOT23                |       |      |       |  |  |
|----------------------|-------|------|-------|--|--|
| Dim                  | Min   | Max  | Тур   |  |  |
| Α                    | 0.37  | 0.51 | 0.40  |  |  |
| В                    | 1.20  | 1.40 | 1.30  |  |  |
| C                    | 2.30  | 2.50 | 2.40  |  |  |
| D                    | 0.89  | 1.03 | 0.915 |  |  |
| F                    | 0.45  | 0.60 | 0.535 |  |  |
| G                    | 1.78  | 2.05 | 1.83  |  |  |
| Η                    | 2.80  | 3.00 | 2.90  |  |  |
| J                    | 0.013 | 0.10 | 0.05  |  |  |
| K                    | 0.903 | 1.10 | 1.00  |  |  |
| K1                   | -     | -    | 0.400 |  |  |
| L                    | 0.45  | 0.61 | 0.55  |  |  |
| М                    | 0.085 | 0.18 | 0.11  |  |  |
| α                    | 0°    | 8°   | -     |  |  |
| All Dimensions in mm |       |      |       |  |  |

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



| Dimensions | Value (in mm) |  |  |
|------------|---------------|--|--|
| Z          | 2.9           |  |  |
| Х          | 0.8           |  |  |
| Υ          | 0.9           |  |  |
| С          | 2.0           |  |  |
| E          | 1.35          |  |  |





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